

APT30DQ120KG Ultrafast Soft Recovery Rectifier Diode

Product Overview

The APT30DQ120KG is a 1200 V, 30 A Ultrafast Soft Recovery Rectifier diode in a TO-220 package.



Features

The following are key features of the APT30DQ120KG device:

- Ultrafast recovery times
- Soft recovery characteristics
- Low forward voltage
- Low leakage current
- Avalanche-energy rated
- RoHS compliant
- AEC-Q101 qualified

Benefits

The following are benefits of the APT30DQ120KG device:

- Low switching losses
- Low noise (EMI) switching
- High switching frequency
- Higher reliability systems
- Increased system power density

Applications

The APT30DQ120KG device is designed for the following applications:

- Power factor correction (PFC)
- Anti-parallel diode
 - Switch-mode power supply
 - Inverters/converters
 - Motor controllers
- Freewheeling diode
 - Switch-mode power supply
 - Inverters/converters
- Snubber/clamp diode



Device Specifications

This section shows the specifications of the APT30DQ120KG device.

Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the APT30DQ120KG device. $T_C = 25$ °C unless otherwise specified.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V _R	Maximum DC reverse voltage	1200	V
V _{RRM}	Maximum peak repetitive reverse voltage		
V _{RWM}	Maximum working peak reverse voltage		
I _{F(AV)}	Maximum average forward current (T _C = 103 °C, duty cycle = 0.5)	30	A
I _{FSM}	Non-repetitive forward surge current (T_J = 45 °C, 8.3 ms)	210	
E _{AVL}	Avalanche energy (1 A, 40 mH)	20	mJ

The following table shows the thermal and mechanical characteristics of the APT30DQ120KG device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min	Тур	Max	Unit
R _{θJC}	Junction-to-case thermal resistance			0.80	°C/W
T _J , T _{STG}	Operating and storage temperature range	-55		175	°C
TL	Lead temperature for 10 seconds			300	
Wt	Package weight		0.07		OZ
			1.9		g
Mounting torque, 6-32 or M3 screw				10	lbf∙in
				1.1	N∙m



Electrical Performance

The following table shows the static characteristics of the APT30DQ120KG device. $T_J = 25$ °C unless otherwise specified.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V _F	Forward voltage	I _F = 30 A		2.8	3.3	V
		I _F = 60 A		3.4		
		Ι _F = 30 A, Τ _J = 125 °C		2.1		
I _{RM} Maximum reverse leakage current		V _R = 1200 V			100	μA
		V _R = 1200 V, T _J = 125 °C			500	
Cj	Junction capacitance	V _R = 200 V		36		pF

The following table shows the dynamic characteristics of the APT30DQ120KG device.

Table 4 •	Dynamic Characteristics	

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
t _{rr}	Reverse recovery time	I _F = 1 A, di _F /dt = -100 A/μs V _R = 30 V		26		ns
t _{rr}	Reverse recovery time	I _F = 30 A, di _F /dt = −200 A/μs V _R = 800 V		320		
Q _{rr}	Reverse recovery charge			545		nC
I _{RRM}	Maximum reverse recovery current			4		A
t _{rr}	Reverse recovery time	I _F = 30 A, di _F /dt = -200 A/μs V _R = 800 V, T _J = 125 °C		435		ns
Q _{rr}	Reverse recovery charge			2100		nC
I _{RRM}	Maximum reverse recovery current			9		A
t _{rr}	Reverse recovery time	I _F = 30 A, di _F /dt = -1000 A/μs V _R = 800 V, T _J = 125 °C		180		ns
Q _{rr}	Reverse recovery charge			2975		nC
I _{RRM}	Maximum reverse recovery current			28		A



Typical Performance Curves

This section shows the typical performance curves of the APT30DQ120KG device.







600 T_J = 125°C V_R = 800V 60A t_{rr}, REVERSE RECOVERY TIME (ns) 500 400 30A 300 15A 200 100 0 200 400 600 800 1000 1200 -di_E/dt, CURRENT RATE OF CHANGE(A/µs)

Figure 2 • Forward Current vs. Forward Voltage

Figure 3 • Reverse Recovery Time vs. Current Rate of Change



Figure 4 • Reverse Recovery Charge vs. Current Rate of Change



Figure 5 • Reverse Recovery Current vs. Current Rate of Change





Figure 6 • Dynamic Parameters vs. Junction Temperature



Figure 7 • Maximum Average Forward Current vs. Case Temperature



Figure 8 • Junction Capacitance vs. Reverse Voltage



Reverse Recovery Overview

The following figure illustrates the diode test circuit of the APT30DQ120KG device.



Figure 9 • Diode Test Circuit

The following figure illustrates the diode reverse recovery waveform and definitions of the APT30DQ120KG device.



Figure 10 • Diode Reverse Recovery Waveform and Definitions

- **1.** I_F Forward conduction current
- 2. $di_F/dt Rate of diode current change through zero crossing$
- **3.** I_{RRM} Maximum reverse recovery current
- 4. t_{rr} Reverse recovery time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero
- 5. Q_{rr} Area under the curve defined by I_{RRM} and t_{rr}



Package Specification

This section shows the package specification of the APT30DQ120KG device.

Package Outline Drawing

The following figure illustrates the TO-220 package outline of the APT30DQ120KG device.



Figure 11 • Package Outline Drawing

The following table shows the TO-220 dimensions and should be used in conjunction with the package outline drawing.

Table 5	• TO-220	Dimensions
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Symbol	Min	Мах	Min	Max	
	(mm)		(Inch)		
А	4.32	4.57	0.170	0.180	
В	1.14	1.40	0.045	0.055	
С	2.50	2.74	0.098	0.108	
D	0.36	0.53	0.014	0.021	



Symbol	Min	Max	Min	Max	
	(mm)		(Inch)		
E	2.65	3.05	0.104	0.120	
F	3.60	3.96	0.142	0.156	
G	14.50	15.60	0.571	0.614	
Н	2.39	3.65	0.094	0.144	
I	6.00	6.80	0.236	0.268	
J	8.40	9.00	0.331	0.354	
К	13.00	14.00	0.512	0.551	
L	1.23	1.39	0.048	0.055	
М	0.69	0.88	0.027	0.035	
Ν	10.00	10.36	0.394	0.408	
0	7.57	7.90	0.298	0.311	
Р	12.20	13.10	0.480	0.516	
Q	2.54 BSC		0.100 BSC		
Terminal 1	CATHODE				
Terminal 2	ANODE				
Terminal 3	CATHODE				